

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1-10. (Cancelled)

11. (Currently Amended) A fabrication method, comprising the steps of:

forming a first layer of silicon at least partially overlying a substantially monolithic body of semiconductor material;

forming a layer of nitride at least partially overlying said first layer of silicon,
said layer of nitride thermally grown;

forming a layer of oxide over said layer of nitride, said layer of oxide deposited by LPCVD at least partially overlying said first layer of silicon;

after said steps of forming said layer of nitride and forming said layer of oxide, ~~but prior to performing any other steps,~~ forming a second layer of silicon at least partially overlying said layer of oxide, said layer of nitride, and said first layer of silicon;

wherein only two layers are present between said first layer of silicon and said second layer of silicon.

12-15. (Cancelled)

16. (New) A fabrication method, comprising the steps of:

forming a first layer of silicon at least partially overlying a substantially monolithic body of semiconductor material;

forming a layer of oxide at least partially overlying said first layer of silicon, said layer of oxide deposited by LPCVD;

forming a layer of nitride over said layer of oxide, said layer of nitride thermally grown;

after said steps of forming said layer of nitride and forming said layer of oxide, forming a second layer of silicon at least partially overlying said layer of oxide, said layer of nitride, and said first layer of silicon;

wherein only two layers are present between said first layer of silicon and said second layer of silicon.